

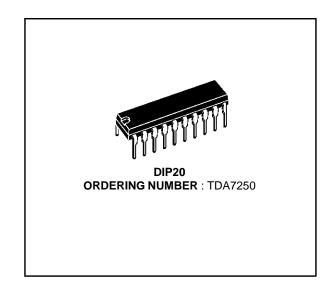
60 W HI-FI DUAL AUDIO DRIVER

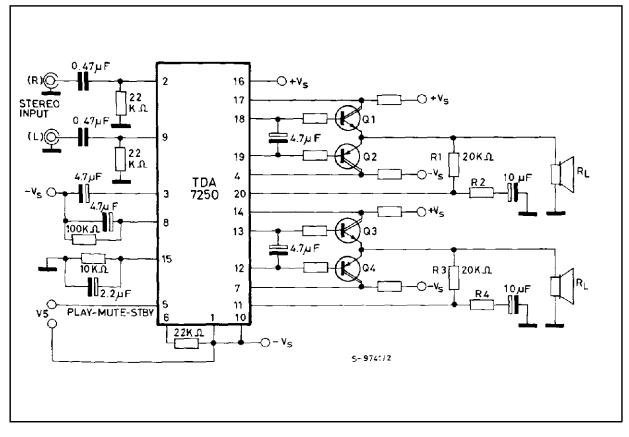
- WIDE SUPPLY VOLTAGE RANGE : 20 TO 90 V (± 10 to ± 45 V)
- VERY LOW DISTORTION
- AUTOMATIC QUIESCENT CURRENT CONTROL FOR THE POWER TRANSISTORS WITHOUT TEMPERATURE SENSE ELEMENTS
- OVERLOAD CURRENT PROTECTION FOR THE POWER TRANSISTORS
- MUTE/STAND-BY FUNCTIONS
- LOW POWER CONSUMPTION
- \blacksquare OUTPUT POWER 60 W/8 Ω AND 100 W/4 Ω

DESCRIPTION

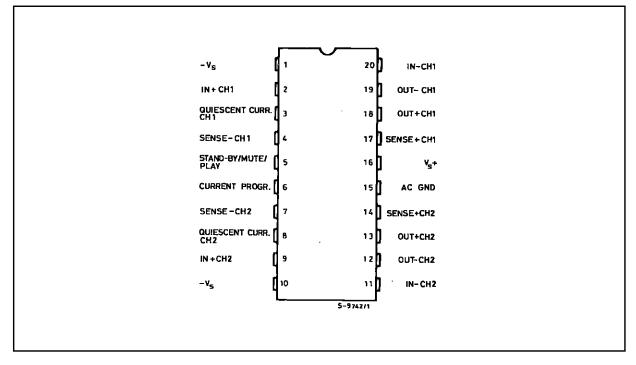
The TDA7250 stereo audio driver is designed to drive two pair of complementary output transistor in the Hi-Fi power amplifiers.

APPLICATION CIRCUIT





PIN CONNECTION (top view)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	100	V
Ptot	Power Dissipation at $T_{amb} = 60 \ ^{\circ}C$	1.4	W
T _j , T _{stg}	Storage and Junction Temperature	- 40 to + 150	°C

THERMAL DATA

Symbol	Parameter		Value	Unit
R _{th j-amb}	Thermal Resistance Junction-ambient	Max.	65	°C/W

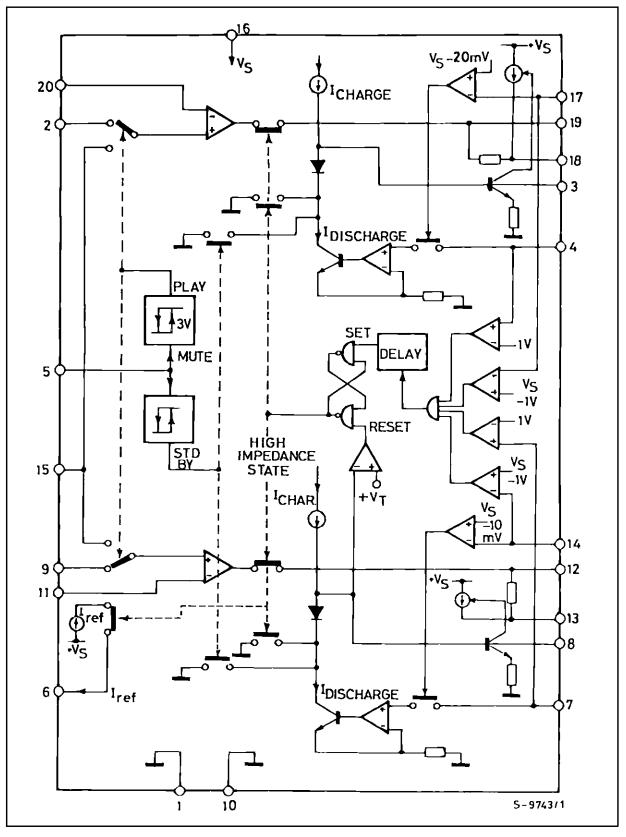


PIN FUNCTIONS

N°	Name	Function			
1	Vs – POWER SUPPLY	Negative Supply Voltage.			
2	NON-INV. INP. CH. 1	Channel 1 Input Signal.			
3	QUIESC. CURRENT CONTR. CAP. CH1	This capacitor works as an integrator, to control the quiescent current to output devices in no-signal conditions on channel 1.			
4	SENSE (–) CH. 1	Negative voltage sense input for overload protection and for automatic quiescent current control.			
5	ST. BY / MUTE / PLAY	Three-functions Terminal. For V _{IN} = 1 to 3 V, the device is in MUTE and only quiescent current flows in the power stages ; - for V _{IN} < 1 V, the device is in STAND-BY mode and no quiescent current is present in the power stages ; - for V _{IN} > 3 V, the devic			
6	CURRENT PROGRAM	High Impedance Power-stages Monitor.			
7	SENSE (–) CH. 2	Negative Voltage Sense Input for Overload Protection and for Automatic Quiescent Current Control.			
8	QUIESC. CURRENT CONTR. CAP. CH. 2	This capacitor works as an integrator, to control the quiescent current to output devices in no-signal conditions on channel 2. If the voltage at its terminals drops under 250 mV, it also resets the device from high-impedance state of output stages.			
9	NON-INV. INP. CH. 2	Channel 2 Input Signals.			
10	V _s – POWER SUPPLY	Negative Supply Voltage.			
11	INVERT. INP. CH. 2	Feedback from Output (channel 2).			
12	OUT (–) CH. 2	Out Signal to Lower Driver Transistor of Channel 2.			
13	OUT (+) CH. 2	Out Signal to Higher Driver Transistor of Channel 2.			
14	SENSE (+) CH. 2	Positive Voltage Sense Input for Overload Protection and for Automatic Quiescent Current Control.			
15	COMMON AC GROUND	AC Input Ground in MUTE Condition.			
16	Vs + POWER SUPPLY	Positive Supply Voltage.			
17	SENSE (+) CH. 1	Positive Voltage Sense Input for Overload Protection and for Automatic Quiescent Current Control.			
18	OUT (+) CH. 1	Out Signal to High Driver Transistor of Channel 1.			
19	OUT (–) CH. 1	Out Signal to Low Driver Transistor of Channel 1.			
20	INVERT. INP. CH. 1	Feedback from Output (channel 1).			



BLOCK DIAGRAM





Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Vs	Supply Voltage		± 10		± 45	V
l _d	Quiescent Drain Current	Stand-by Mode		8		mA
		Play Mode		10	14	
l _b	Input Bias Current			0.2	1	μA
Vos	Input Offset Voltage			1	± 10	mV
l _{os}	Input Offset Current			100	200	nA
Gv	Open Loop Voltage Gain	f = 100 Hz		90		dB
		f = 10 kHz		60		
e _N	Input Noise Voltage	$R_{G} = 600 \Omega$ B = 20 Hz to 20 kHz		3		μV
SR	Slew Rate			10		V/µs
d	Total Harmonic Distortion	$G_v = 26 \text{ dB}, P_o = 40 \text{ W}$ f = 1 kHz f = 20 kHz		0.004 0.03		%
Vopp	Output Voltage Swing			60		Vpp
Po	Output Power (*)	$ \begin{array}{l} {\sf V}_{\sf s} = \pm \; 35 \; {\sf V}, \; {\sf R}_{\sf L} = 8 \; \Omega \\ {\sf V}_{\sf s} = \pm \; 30 \; {\sf V}, \; {\sf R}_{\sf L} = 8 \; \Omega \\ {\sf V}_{\sf s} = \pm \; 35 \; {\sf V}, \; {\sf R}_{\sf L} = 4 \; \Omega \end{array} $		60 40 100		W W W
l _o	Output Current			± 5		mA
SVR	Supply Voltage Rejection	f = 100 Hz		75		dB
Cs	Channel Separation	f = 1 kHz		75		dB

ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C, V_s = \pm 35 V, play mode, unless otherwise specified)

MUTE / STANDBY/ PLAY FUNCTIONS

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
li	Input Current (pin 5)			0.1		μA
V _{th}	Comparator Standby / Mute Threshold (**)		1.0	1.25	1.5	V
Н	Hysteresis Standby / Mute			200		mV
Vth	Comparator Mute / Play Threshold (**)		2.4	3.0	3.6	V
Н	Hysteresis Mute / Play			300		mV
	Mute Attenuation	f = 1 kHz		60		dB
Vi	Input Voltage Max. (pin 5)		12 (**)			V

(*) Application circuit of fig. 1 f = 1 KHz; d = 0.1 %; $G_v = 26 \text{ dB}$. (**) Referred to $- V_s$.

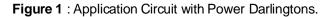
CURRENT SURVEY CIRCUITRY

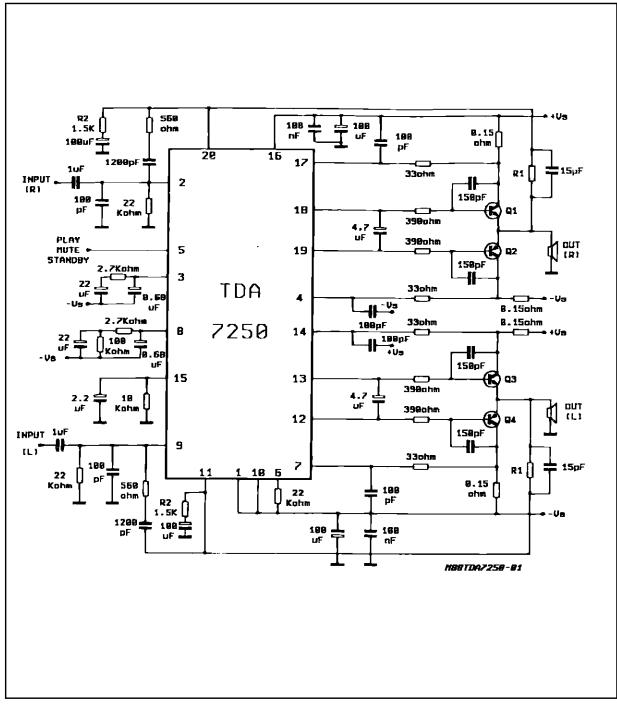
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
	Comparator Reference	to + V _S	0.8	1	1.4	V
		to – Vs	0.8	1	1.4	V
t _d	Delay Time		10			μs

QUIESCENT CURRENT CONTROL

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
	Capacitor Current	Charge Discharge	30 250	60 500		μA uA
	Comparator Reference	to + V_S	10	20	25	mV
	-	to – Vs		10		mV







Note : Q1/Q2 = Q3/Q4 = TIP 142/TIP147GV = 1 + R1/R2



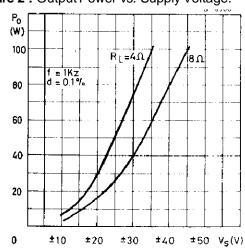
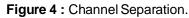


Figure 2 : Output Power vs. Supply Voltage.



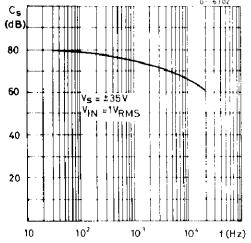
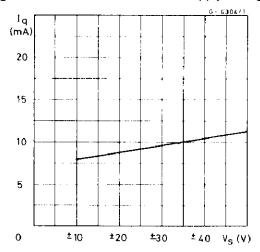
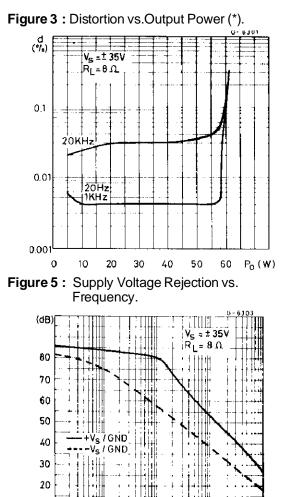


Figure 6: Quiescent Current vs. Supply Voltage.





 $10 10^2 10^3 10^4 f(Hz)$

10

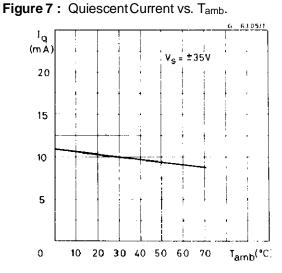
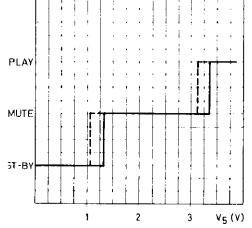


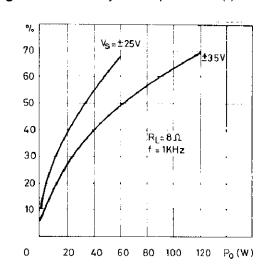


Figure 8 : Total Dissipated Power vs. Output Power (*). P_{tot} (W) RL=801 f = 1KHz 60 v_s=±35V 50 40 1 ł 30 ±25V 20 10 0 20 40 60 80 100 $\mathsf{P}_{\mathbf{0}}(\mathsf{W})$ Figure 10: Play-mute Standby Operation. 6308



(*) Complete circuit

Figure 9: Efficiency vs. Output Power (*).





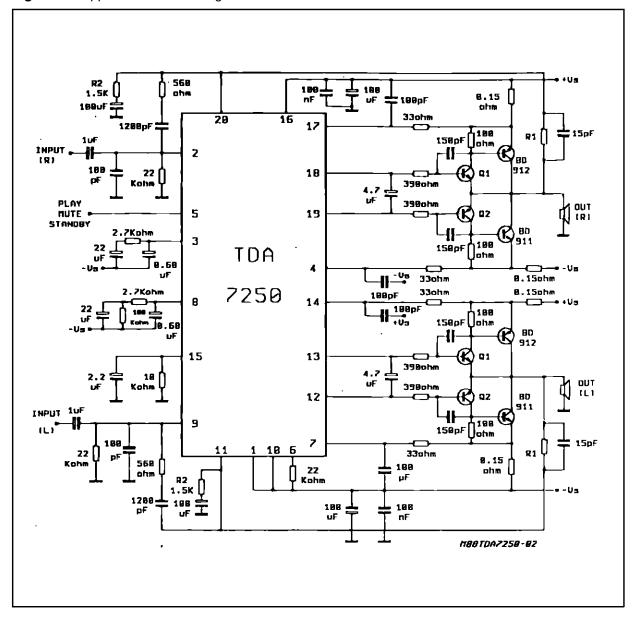


Figure 11 : Application Circuit Using Power Transistors.

Figure 12 : Suggested Transistor Types for Various Loads and Powers.

 $R_L = 8 \Omega$

15W	+30W	+50W	+70W
BDX	BDX	BDW	TIP
53/54A	53/54B	93/94B	142/147

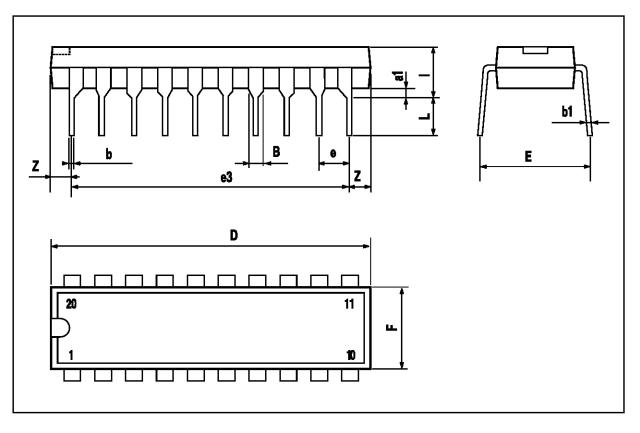
$T_L = 4 \Omega$	
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30W	+50W	+90W	+130W
BDW 93/94A	BDW 93/94B	BDV 64/65B	MJ 11013/11014



DIP20 PACKAGE MECHANICAL DATA

DIM.		mm			inch	
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
В	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			24.80			0.976
E		8.80			0.346	
е		2.54			0.100	
e3		22.86			0.900	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050





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